

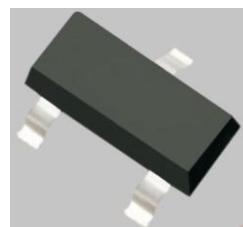
BC817-16/-25/-40

NPN Transistor

Features

- ◆ For switching, AF driver and amplifier applications
- ◆ These transistors are subdivided into three groups -16, -25 and -40, according to their current gain. As complementary types the PNP transistors BC817 are recommended

SOT-23



1 Base 2. Emitter 3. Collector

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	45	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	0.5	A
Power Dissipation	P_C	0.3	W
Operation Junction and Storage Temperature Range	T_J, T_{STG}	150,-55 to 150	$^\circ\text{C}$

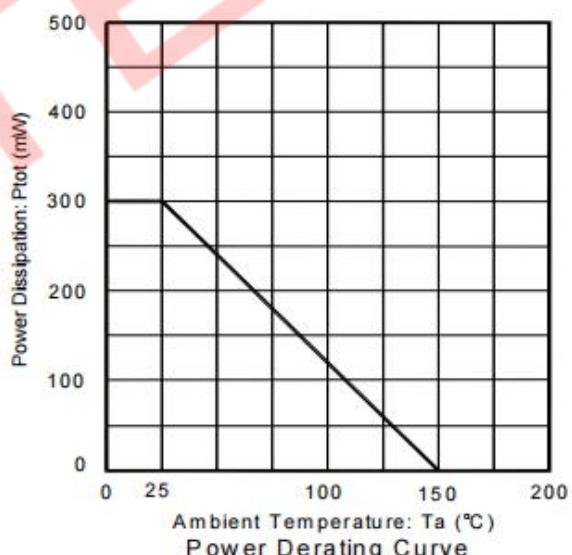
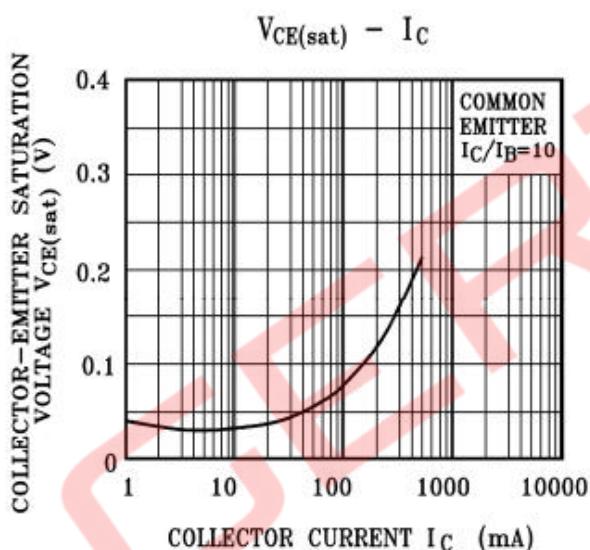
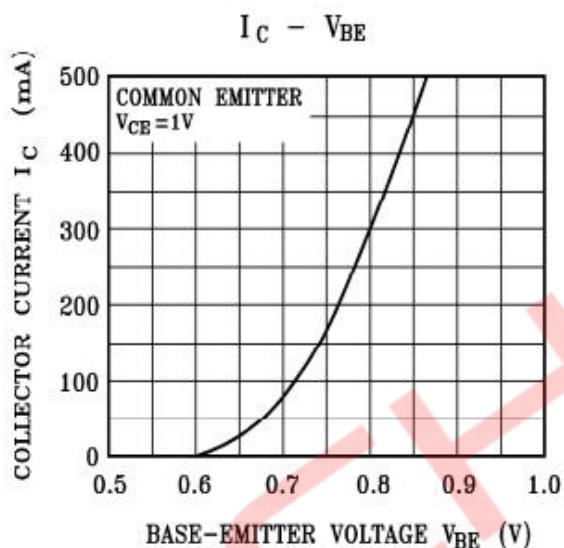
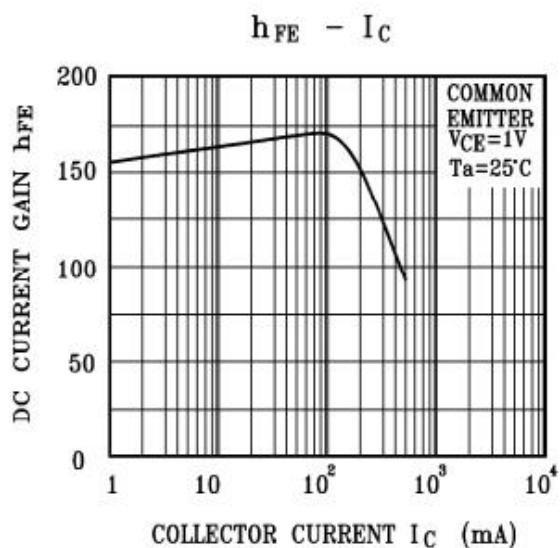
Electrical Characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 20\text{V}$			100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}$			100	nA
DC current gain	h_{FE1}	$V_{CE} = 1\text{V}, I_C = 100\text{mA}$	100		250	
	h_{FE2}		160		400	
	h_{FE3}		250		600	
	h_{FE4}	$V_{CE} = 1\text{V}, I_C = 500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			0.7	V
Base-emitter saturation voltage	$V_{BE(on)}$	$I_C = 500\text{mA}, V_{CE} = 1\text{V}$			1.2	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=10\text{mA}, f=50\text{MHz}$	100			MHZ
Collector Base Capacitance	Cbo	$V_{CB}=10\text{V}, f=1\text{MHz}$		9		pF

Marking

RANK	BC817-16	BC817-25	BC817-40
Marking	6CQ	6CS	6CT

Typical Characteristics Curves



Package Outline

SOT-23

